Notice of Allowability	Application No.	Applicant(s)	
	10/724,687	LEE ET AL.	
	Examiner	Art Unit	
	ANH PHUNG	2824	
The MAILING DATE of this communication apper All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED or other appropriate comm GHTS. This application is	in this application. If not included in the in	uded e course. THIS
1. This communication is responsive to			
2. ☐ The allowed claim(s) is/are 1-20.			
3. $\[\]$ The drawings filed on $\[\underline{\textit{02 December 2003}} \]$ are accepted by	the Examiner.		
 4. Acknowledgment is made of a claim for foreign priority una) All b) Some* c) None of the: Certified copies of the prioritydocuments have Certified copies of the priority documents have Copies of the certified copies of the priority documents have Copies of the certified copies of the priority documents have Thernational Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE 	been received. been received in Applicate cuments have been received.	ion No ed in this national stage appli	
5. A SUBSTITUTE OATH OR DECLARATION must be submi INFORMAL PATENT APPLICATION (PTO-152) which give			NOTICE OF
6. CORRECTED DRAWINGS (as "replacement sheets") mus	t be submitted.		
(a) ☐ including changes required by the Notice of Draftspers	on's Patent Drawing Revie	ew (PTO948) attached	
1) hereto or 2) to Paper No./Mail Date			
(b) including changes required by the attached Examiner's Paper No./Mail Date	s Amendment / Comment o	or in the Office action of	
ldentifying Indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in th			the back) of
7. DEPOSIT OF and/or INFORMATION about the depos attached Examiner's comment regarding REQUIREMENT I			Note the
Attachment(s)			
1. Notice of References Cited (PTO-892)	5. Notice of Ir	nformal Patent Application (P	TO-152)
2. Notice of Draftperson's Patent Drawing Review (PTO 948)	Paper No.	Summary (PTO-413), /Mail Date	
3. ☐ Information Disdosure Statements (PTO-1449 or PTO/SB/08 Paper No./Mail Date 2/5/04		Amendment/Comment	
 Examiner's Comment Regarding Requirement for Deposit of Biological Material 	_	Statement of Reasons for All	lowance
5. Biological ividuoi idi	9. ⊠ Other <u>Sear</u>	ANH PHUNG	
U.S. Patent and Trademark Office	PRI	MARY EXAMINER	

U.S. Patent and Trademark Office PTOL-37 (Rev. 1-04)

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Detailed Action

1. In response to the U.S. Patent Application Serial No. 10/724,687 filed on December 2, 2003, claims **1-20** are pending in the application.

Priority

2. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Information Disclosure Statement

This office acknowledges receipt of the following items from the Applicant:
 Information Disclosure Statement (IDS) filed on February 5, 2004.
 Information disclosed and listed on PTO 1449 was considered.

Examiner's Statement of Reasons for Allowance

4. Claims **1-20** are allowed.

Nii (US 6,590,802), Wong (US 6,341,083) and Hobson (US 5,754,468) disclose a dual port semiconductor memory device similar to that of the present application, but fail to teach:

"wherein the first PMOS transistor and the second PMOS transistor are disposed in the P+-type active region of the N-well area; and the first NMOS transistor, the second NMOS transistor, the third NMOS transistor, the fourth NMOS transistor, the fifth NMOS transistor, and the sixth NMOS transistor are formed in the n+-type active region of the contiguous P-well area" as claim in the independent claim 1; or

"wherein the first PMOS transistor and the second PMOS transistor are disposed in the P+-type active region of the N-well area; and the first NMOS transistor, the

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second NMOS transistor, the third NMOS transistor, the fourth NMOS transistor, and the fifth NMOS transistor are formed in the n+-type active region of the contiguous P-well area" as claim in the independent claim 11.

Any comments considered necessary by applicants must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comment on Statement of Reasons for Allowance".

Conclusion

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to **ANH PHUNG** whose telephone number is **(571) 272-1883**. The examiner can normally be reached on Monday-Friday from 8:00 AM to 4:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, **RICHARD ELMS**, can be reached on **(571) 272-1869**. The fax phone number for the organization where this application or proceeding is assigned is **(703) 872-9306**.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should

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you have questions on access to the Private PAIR system, contact the Electronic

Business Center (EBC) at 866-217-9197 (toll-free).

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